

## NCE N-Channel Super Trench Power MOSFET

### Description

The NCEP1580GU uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(on)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

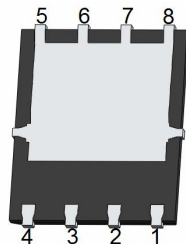
- $V_{DS} = 150V, I_D = 80A$   
 $R_{DS(on)} = 12.0m\Omega$  (typical) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100% ΔVds TESTED!**

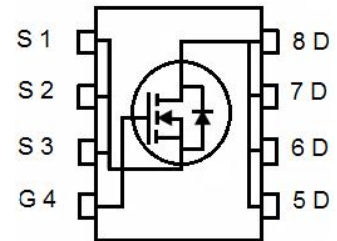
### DFN 5X6



Top View



Bottom View



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
P1580GU	NCEP1580GU	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	150	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	80	A
Drain Current-Continuous ( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	52	A
Pulsed Drain Current	$I_{DM}$	320	A
Maximum Power Dissipation	$P_D$	170	W
Derating factor		1.36	W/°C
Single pulse avalanche energy (Note 1)	$E_{AS}$	650	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.73	°C/W
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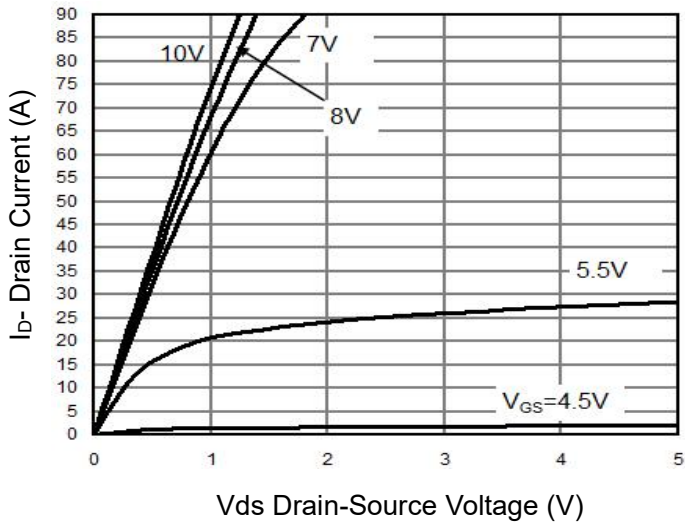
## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =150V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	-	4.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	-	12	14.5	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =40A	-	58	-	S
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =75V, V <sub>GS</sub> =0V, F=1.0MHz	-	2200	-	PF
Output Capacitance	C <sub>OSS</sub>		-	289	-	PF
Reverse Transfer Capacitance	C <sub>RSS</sub>		-	11.2	-	PF
<b>Switching Characteristics</b> <small>(Note 2)</small>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =75V, I <sub>D</sub> =40A V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	12.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	3.8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	14	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3.5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =75V, I <sub>D</sub> =40A, V <sub>GS</sub> =10V	-	40	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	14.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	10	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =40A	-	-	1.2	V
Diode Forward Current	I <sub>S</sub>		-	-	80	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 40A di/dt = 100A/μs	-	47	-	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	55	-	nC

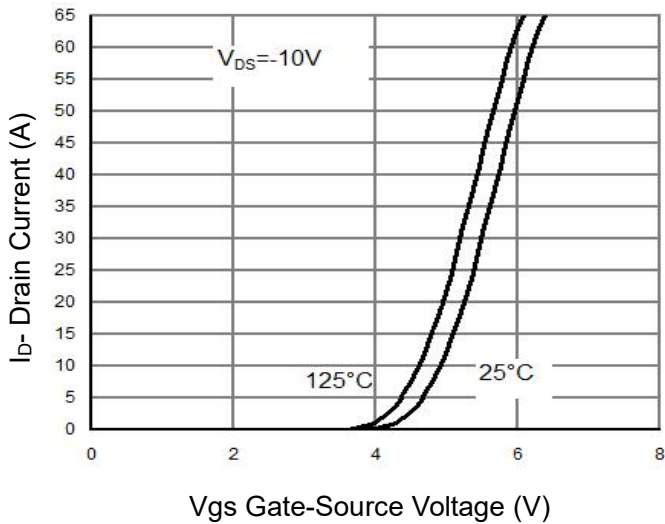
### Notes:

1. E<sub>AS</sub> condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J</sub>(MAX)=150° C. The SOA curve provides a single pulse rating.

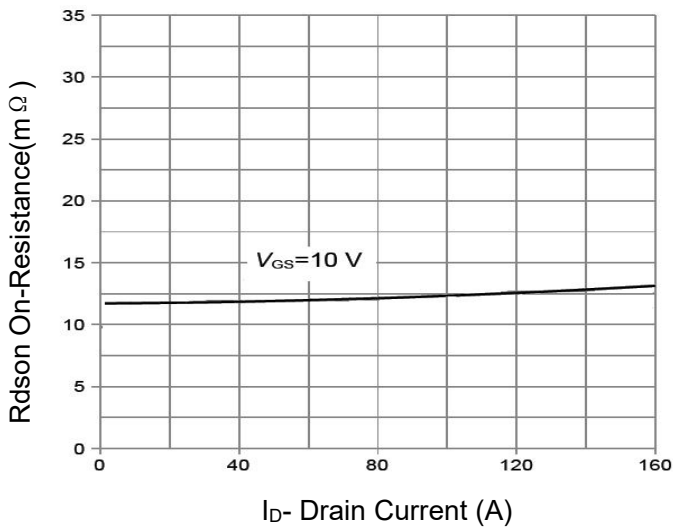
## Typical Electrical and Thermal Characteristics



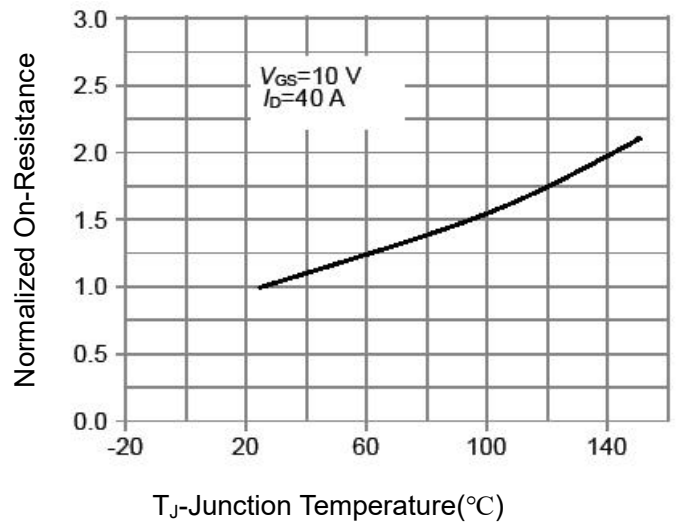
**Figure 1 Output Characteristics**



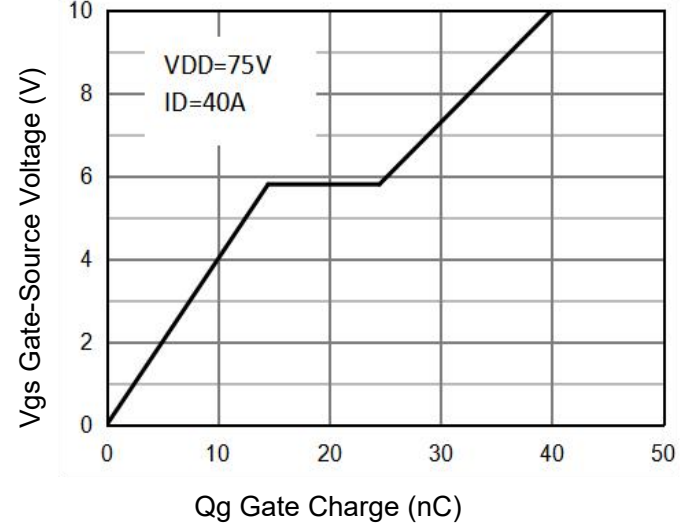
**Figure 2 Transfer Characteristics**



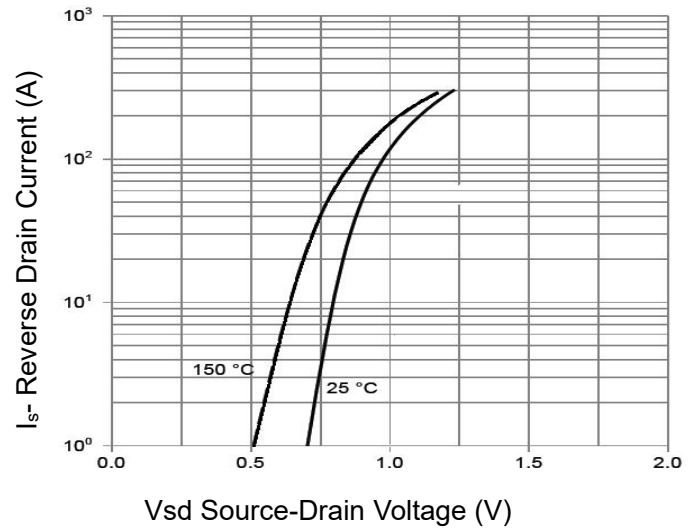
**Figure 3 Rdson- Drain Current**



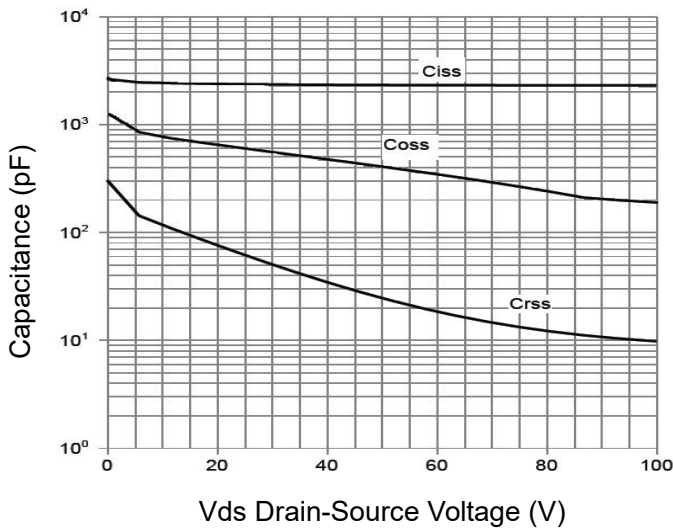
**Figure 4 Rdson-Junction Temperature**



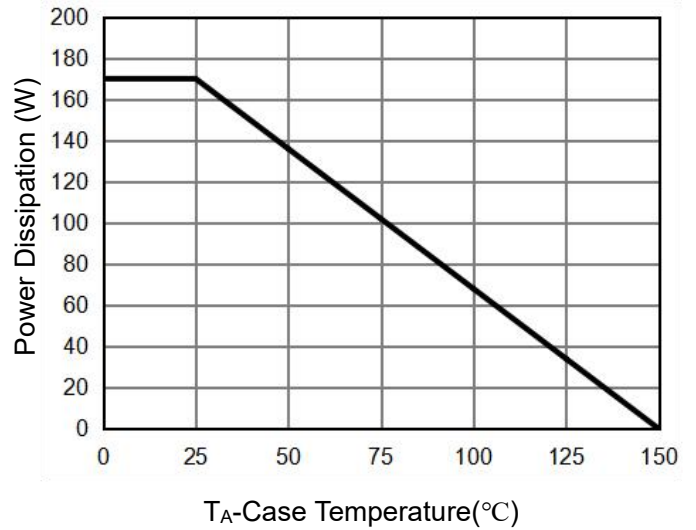
**Figure 5 Gate Charge**



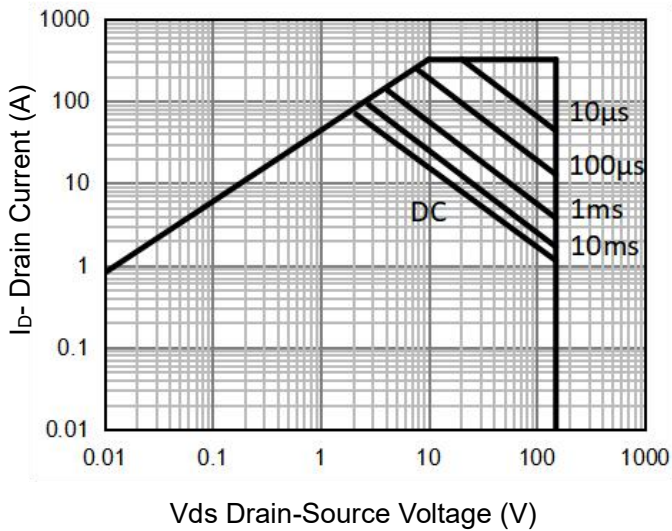
**Figure 6 Source- Drain Diode Forward**



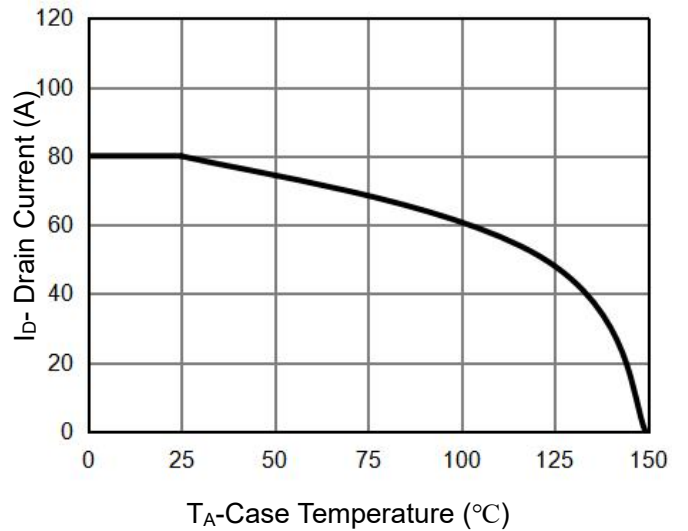
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



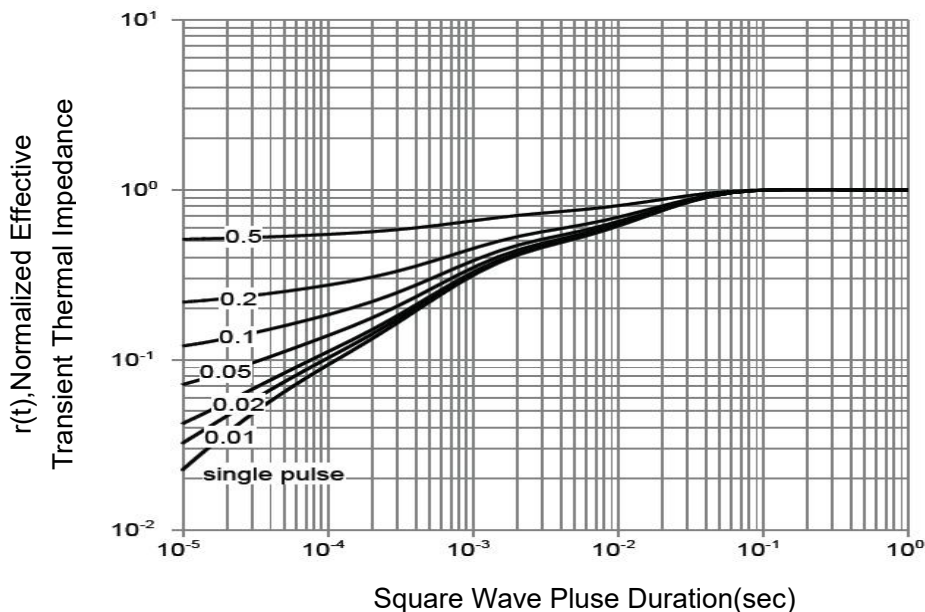
TA-Case Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area** (Note 3)

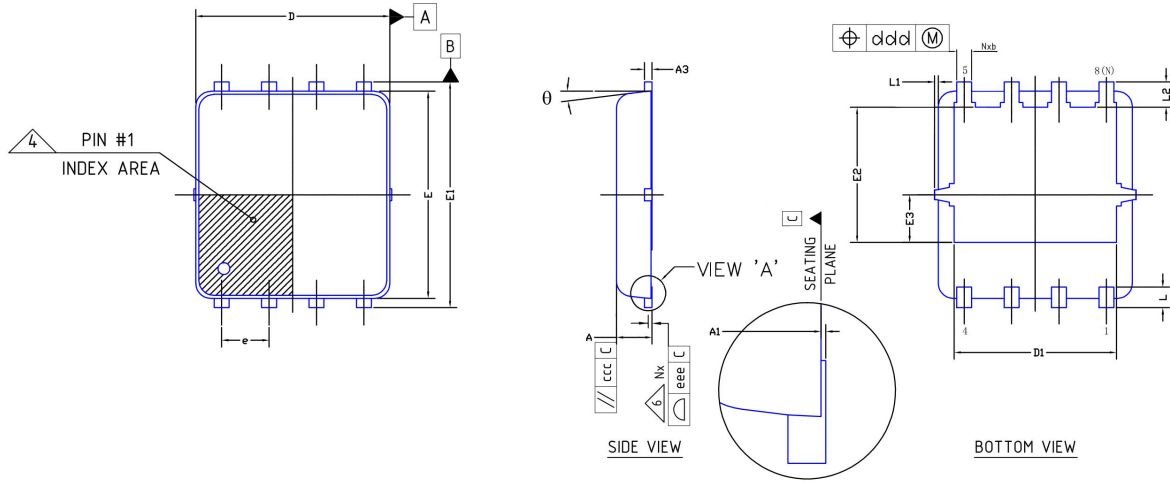


TA-Case Temperature (°C)  
**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## DFN5X6-8L(f) Package Information

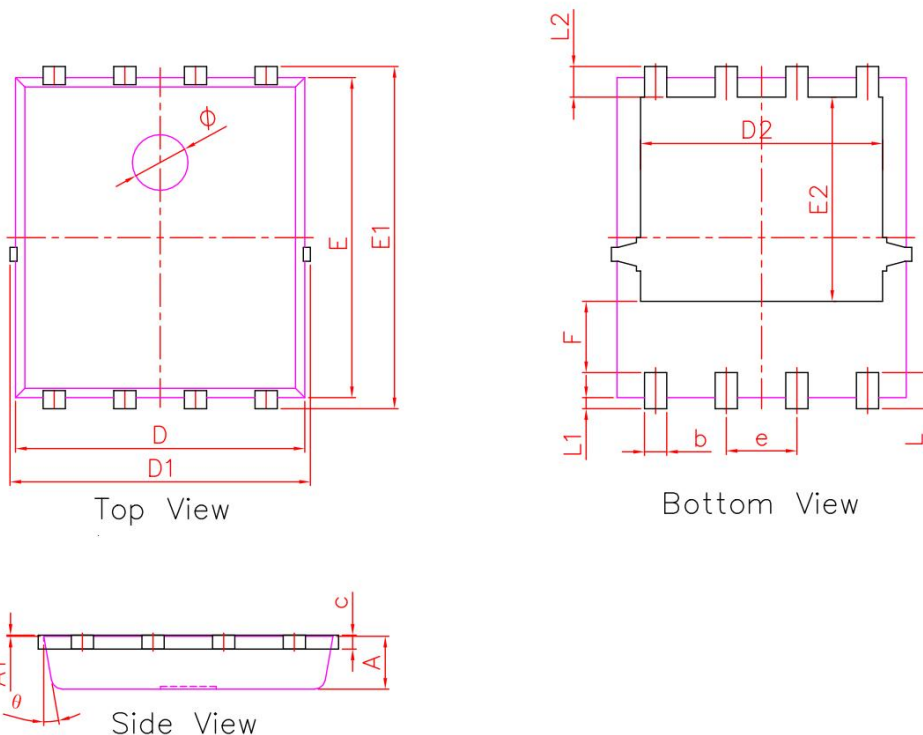


Dimension Table				
Thickness Symbol	V			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	0.85	0.95	1.00	
A1	0.00	---	0.05	
A3	---	0.2 Ref	---	
b	0.30	0.40	0.50	
D	5.20 BSC			
E	5.55 BSC			
e	1.27 BSC			
D1	4.25	4.35	4.45	
E1	5.95	6.05	6.15	
E2	3.525	3.625	3.725	
E3	1.175	1.275	1.375	
L	0.45	0.55	0.65	
L1	0	---	0.15	
L2	0.68 REF			
θ	0°	---	10°	
aaa	0.05			
bbb	0.10			
ccc	0.10			
ddd	0.05			
eee	0.08			
N	8			3
ND	4			5
NOTES	1,2			
LF PART NO.	445831/445897			

NOTE:

1. Dimensioning and tolerancing conform to ASME Y14.5-2009.
2. All dimensions are in millimeters.
3. N is the total number of terminals.
4. The location of the marked terminal #1 identifier is within the hatched area.
5. NE refers to the maximum number of terminals E side.
6. Coplanarity applies to the terminals and all other bottom surface metallization.

## DFN5X6-8L(E) Package Information



PDFN5X6-8L			
DIM.	MIN.	NOM.	MAX.
A	0.90	0.95	1.00
A1	0.00	0.02	0.05
b	0.35	0.40	0.50
c	0.20	0.25	0.30
D	5.10	5.20	5.30
D1	5.10	5.40	5.50
D2	4.25	4.35	4.45
e	1.27 BSC		
E	5.70	5.75	5.80
E1	6.00	6.15	6.30
E2	3.57	3.67	3.77
F	1.18	1.28	1.38
L	0.55	0.65	0.75
L1	0.15	0.20	0.25
L2	0.45	0.55	0.65
$\phi$	0.90	1.00	1.10
$\theta$	8°	10°	12°
All dimensions in millimeters			

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